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Journal of Crystal Growth 169 (1996) 803–810

JOURNAL OF CRYSTAL GROWTH

Author index

Aarik, J., A. Aidla, V. Sammelselg, H. Siimon and T. Uustare, Control of thin film structure by reactant pressure in atomic layer deposition of TiO_2 169 (1996) 496
Abbaschian, R., see Saghir, M.Z. 169 (1996) 110
Aguiló, M., see Solé, R. 169 (1996) 600
Ahuja, M.N., see Sabharwal, S.C. 169 (1996) 304
Aidla, A., see Aarik, J. 169 (1996) 496
Alexandru, H.V., Growth kinetic of prismatic faces of ammonium dihydrogen phosphate crystal in solutions 169 (1996) 347
Alvarez, J.C., see Sokolov, N.S. 169 (1996) 40
Androussi, Y., A. Lefebvre, T. Benabbas, P. François, C. Delamarre, J.Y. Laval and A. Dubon, Dislocation introduction in the initial stages of MBE growth of highly strained $In_{0.30}Ga_{0.70}As/GaAs$ structures 169 (1996) 209
Artymowicz, D.M., B.M. Lairson and B.M. Clemens, Formation of ordered tetragonal PtCo from epitaxial Pt/Co multilayers 169 (1996) 83
Ausloos, M., see Vandewalle, N. 169 (1996) 79

Badaljan, E., see Pfeifer, J. 169 (1996) 727
Badescu, V. and M. Momirlan, Statistics of TiO_2 crystal growth in air on a metallic surface heated at temperatures in the range of 900–1100°C 169 (1996) 309
Baker, M. and M.B. Baker, A model for the ice–vapor interface at equilibrium 169 (1996) 393
Baker, M.B., see Baker, M. 169 (1996) 393
Baranowski, J.M., see Leszczynski, M. 169 (1996) 235
Basmaji, P., see González-Borrero, P.P. 169 (1996) 424
Baumgartl, J. and G. Müller, The use of magnetic fields for damping the action of gravity fluctuations (g-jitter) during crystal growth under microgravity 169 (1996) 582
Benabbas, T., see Androussi, Y. 169 (1996) 209
Bermúdez, V., P.S. Dutta, M.D. Serrano and E. Diéguez, In situ poling of $LiNbO_3$ bulk crystal below the Curie temperature by application of electric field after growth 169 (1996) 409
Bignazzi, A., E. Grilli, M. Guzzi, M. Radice, A. Bosacchi, S. Franchi and R. Magnanini, Low temperature photoluminescence of tellurium-doped GaSb grown by molecular beam epitaxy 169 (1996) 450
Bliss, D.F., see Zhang, H. 169 (1996) 250
Bockowski, M., see Leszczynski, M. 169 (1996) 235
Boistelle, R., see El Moussaouiti, M. 169 (1996) 118
Boistelle, R., see Seyssiecq, I. 169 (1996) 124
Borodi, Gh., see Darabont, Al. 169 (1996) 89
Bosacchi, A., see Bignazzi, A. 169 (1996) 450
Botha, J.R. and A.W.R. Leitch, Influence of growth interruption on the heterointerface morphology of InGaAs/GaAs strained quantum wells 169 (1996) 629
Bouhaouss, A., see El Moussaouiti, M. 169 (1996) 118
Bovin, J.-O., see Deppert, K. 169 (1996) 13
Brown, M., see Steiner, B. 169 (1996) 1

Čabrić, B., N. Danilović and B. Žižić, A crystallization cooler in a chamber furnace 169 (1996) 199
Calixto, E., P.J. Sebastian and A. Fernandez, Electro/electroless deposition and characterization of Cu–In precursors for CIS ($CuInSe_2$) films 169 (1996) 287
Cao, J.Y., see Li, B. 169 (1996) 480
Carstanjen, H.-J., see Scholz, U. 169 (1996) 575
Chait, A., see Pines, V. 169 (1996) 798
Chani, V.I., K. Shimamura, S. Endo and T. Fukuda, $K(M_{1/3}Nb_{2/3})OAsO_4$ (M = Mg, Zn) crystals with structure of $KTiOPO_4$ 169 (1996) 604
Charnley, N.R., see Chowdhury, A.J.S. 169 (1996) 405
Chauhan, A.K., see Sabharwal, S.C. 169 (1996) 304
Chen, F.R., see Chou, W.C. 169 (1996) 747
Chen, X.Q., see Li, B. 169 (1996) 480
Chern-Yu, K., see Chou, W.C. 169 (1996) 747
Cherng, Y.T., see Sze, P.W. 169 (1996) 27
Chernov, A.A., see Coriell, S.R. 169 (1996) 773
Chiang, T.Y., see Chou, W.C. 169 (1996) 747
Choe, K.S., Y.H. Choi and W.S. Yi, Complementary non-destructive optical methods for characterizing $Al_xGa_{1-x}As$ HMESFET heterostructures 169 (1996) 227
Choi, Y.H., see Choe, K.S. 169 (1996) 227
Chou, W.C., F.R. Chen, T.Y. Chiang, H.Y. Shin, C.Y. Sun, C.M. Lin, K. Chern-Yu, C.T. Tsai and D.S. Chuu, Growth and characterization of $Cd_{1-x-y}Zn_xMn_yTe$ crystals 169 (1996) 747
Chowdhury, A.J.S., N.R. Charnley, F.R. Wondre, A.V. Volkozub, P.A.J. de Groot, B.M.R. Wanklyn and J.W. Hodby, Growth

of BSCCO 2212 crystals in flat dish-shaped crucibles 169 (1996) 405
Chu, J.H., see Li, B. 169 (1996) 480
Chuu, D.S., see Chou, W.C. 169 (1996) 747
Clemens, B.M., see Artymowicz, D.M. 169 (1996) 83
Cloots, R., see Vandewalle, N. 169 (1996) 79
Colson, H.G., see Kidd, P. 169 (1996) 649
Coriell, S.R., B.T. Murray, A.A. Chernov and G.B. McFadden, Step bunching on a vicinal face of a crystal growing in a flowing solution 169 (1996) 773
Cui, F.Z., L.F. Zhou, H. Cui, C.L. Ma, H.B. Lu and H.D. Li, Phase diagram for controlled crystallization of calcium phosphate under acidic organic monolayers 169 (1996) 557
Cui, H., see Cui, F.Z. 169 (1996) 557

Dabringhaus, H., see Helmrich, R. 169 (1996) 279
Dai, L.R., see Han, J.H. 169 (1996) 129
Danilović, N., see Čabrić, B. 169 (1996) 199
Darabont, Al., C. Neamţu, S.I. Fărcaş and Gh. Borodi, Growth of pure and doped $KMgF_3$ single crystals 169 (1996) 89
De Groot, P.A.J., see Chowdhury, A.J.S. 169 (1996) 405
Delamarre, C., see Androussi, Y. 169 (1996) 209
De Maeyer, E.A.P., R.M.H. Verbeeck and I.Y. Pieters, Influence of the solution composition on the stoichiometry of Na^+- and of K^+-containing carbonated apatites obtained by the hydrolysis of monetite 169 (1996) 539
Demo, P., see Kožíšek, Z. 169 (1996) 413
Deppert, K., J.-O. Bovin, J.-O. Malm and L. Samuelson, A new method to fabricate size-selected compound semiconductor nanocrystals: aerotaxy 169 (1996) 13
Desai, D.G., see Sabharwal, S.C. 169 (1996) 304
De Yoreo, J.J., see Smolski, I. 169 (1996) 741
Díaz, F., see Solé, R. 169 (1996) 600
Dieckmann, R., see Tsai, T.-L. 169 (1996) 759
Dieckmann, R., see Tsai, T.-L. 169 (1996) 764
Diéguez, E., see Bermúdez, V. 169 (1996) 409
Domagala, J., see Leszczynski, M. 169 (1996) 235
Dost, S., see Kimura, M. 169 (1996) 697
Dravid, V., see Zhang, K. 169 (1996) 73
Driver, R.D., see Salim, S. 169 (1996) 443
Dubon, A., see Androussi, Y. 169 (1996) 209
Dunstan, D.J., see Kidd, P. 169 (1996) 649
Durygin, A., see Frukacz, Z. 169 (1996) 98
Dutta, P., see Mukherjee, D.K. 169 (1996) 136
Dutta, P.S., see Bermúdez, V. 169 (1996) 409

El Moussaouiti, M., R. Boistelle, A. Bouhaouss and J.P. Klein, Agglomeration kinetics of calcium sulphate hemihydrate crystals in sulpho-phosphoric solutions 169 (1996) 118
Endo, S., see Chani, V.I. 169 (1996) 604
Endoh, Y., see Imaizumi, M. 169 (1996) 293
Fărcaş, S.I., see Darabont, Al. 169 (1996) 89
Fatemi, M., Characterization of semiconductor strained layers grown on (110)-type substrates by high-resolution X-ray diffractometry 169 (1996) 261
Feng, S., see Lu, L. 169 (1996) 637
Feng, S., see Lu, L. 169 (1996) 643
Fernandez, A., see Calixto, E. 169 (1996) 287
Flytzani-Stephanopoulos, M., see Krueger, C.W. 169 (1996) 51
Franchi, S., see Bignazzi, A. 169 (1996) 450
François, P., see Androussi, Y. 169 (1996) 209
Frukacz, Z., T. Lukasiewicz, A. Matkowskii, I. Pracka, D. Sugak, I. Solskii, L. Vasylechko and A. Durygin, Effects of ionizing radiation on the optical absorption of $LiNbO_3$ and $YAlO_3$ single crystals 169 (1996) 98
Fujiwara, S., T. Kotani, K. Matsumoto and T. Shirakawa, Crystal growth of ZnSe by PVT using a semi-open ampule 169 (1996) 660
Fuke, S., see Takano, Y. 169 (1996) 621
Fukuda, T., see Kawaguchi, T. 169 (1996) 94
Fukuda, T., see Takeda, H. 169 (1996) 503
Fukuda, T., see Chani, V.I. 169 (1996) 604
Furukawa, Y., see Nada, H. 169 (1996) 587

García, R., see Kidd, P. 169 (1996) 649
García-Ruiz, J.M., see Otálora, F. 169 (1996) 361
Gastev, S.V., see Sokolov, N.S. 169 (1996) 40
Gavaldà, Jna., see Solé, R. 169 (1996) 600
Ge, W., see Lu, L. 169 (1996) 637
Ge, W., see Lu, L. 169 (1996) 643
Geiger, M., D. Ottenwälder, F. Scholz, M. Glanz, C. Recker, J. Winterfeld and H. Schumann, Bis-phosphino-methane: a new precursor for metalorganic vapor phase epitaxy of phosphides 169 (1996) 625
Geng, X., see Wu, X.-B. 169 (1996) 786
Geszti, O., see Pfeifer, J. 169 (1996) 727
Gillies, D., see Palosz, W. 169 (1996) 20
Glanz, M., see Geiger, M. 169 (1996) 625
Gomei, Y., see Murooka, K.-i. 169 (1996) 485
Gómez-Morales, J., J. Torrent-Burgués and R. Rodríguez-Clemente, Nucleation of calcium carbonate at different initial pH conditions 169 (1996) 331
Gómez-Morales, J., see Rodríguez-Clemente, R. 169 (1996) 339
González-Borrero, P.P., D.I. Lubyshev, E. Marega Jr., E. Petitprez and P. Basmaji, Self-organized InGaAs quantum dots grown by molecular beam epitaxy on (100), (711)A/B, (511)A/B, (311)A/B, (211)A/B, and (111)A/B oriented GaAs 169 (1996) 424
González, D., see Kidd, P. 169 (1996) 649
González, L., see Kidd, P. 169 (1996) 649
González-Sanz, F., see Kidd, P. 169 (1996) 649
González, Y., see Kidd, P. 169 (1996) 649
Goodhew, P.J., see Kidd, P. 169 (1996) 649
Gotoh, Y., see Tanaka, Y. 169 (1996) 299

Grasza, K., see Palosz, W. 169 (1996) 20
Grilli, E., see Bignazzi, A. 169 (1996) 450
Grzegory, I., see Leszczynski, M. 169 (1996) 235
Guérin, R., see Le Marec, C. 169 (1996) 147
Guo, Z.-Y., see Wu, X.-B. 169 (1996) 786
Guzzi, M., see Bignazzi, A. 169 (1996) 450

Habuka, H., T. Nagoya, M. Mayusumi, M. Katayama, M. Shimada and K. Okuyama, Model on transport phenomena and epitaxial growth of silicon thin film in $SiHCl_3$–H_2 system under atmospheric pressure 169 (1996) 61
Haldenwang, P., see Le Marec, C. 169 (1996) 147
Hamadeh, H., see Taudt, W. 169 (1996) 243
Han, J.H., Z.W. Sun, L.R. Dai, J.C. Xie and W.R. Hu, Experiment on the thermocapillary convection of a mercury liquid bridge in a floating half zone 169 (1996) 129
Han, Y., see Liu, W.J. 169 (1996) 534
Hara, K., see Watanabe, K. 169 (1996) 223
Harada, J., see Sokolov, N.S. 169 (1996) 40
Harris Jr., J.S., see Hung, C.Y. 169 (1996) 201
Harris Jr., J.S., see Lee, H. 169 (1996) 689
Hashimoto, S., A. Yamaguchi and S.-i. Oya, Formation of needle-like β-Ca_2SiO_4 crystals by vapor phase reaction 169 (1996) 376
Hashimoto, T., O. Imafuji, M. Ishida, Y. Terakoshi, T. Sugino, A. Yoshikawa, K. Itoh and J. Shirafuji, Inheritance of zinc-blende structure from 3C–SiC/Si(001) substrate in growth of GaN by MOCVD 169 (1996) 185
Hayakawa, Y., S. Iida, T. Sakurai, H. Yanagida, M. Kikuzawa, T. Koyama and M. Kumagawa, Epitaxial lateral overgrowth of InGaAs on patterned GaAs substrates by liquid phase epitaxy 169 (1996) 613
He Youping, Su Genbo, Yu Xianchun, Li Zhengdong, Huang Bingrong, Jang Rihong and Zhao Qingran, Growth of α-nickel sulphate hexahydrate for ultraviolet filters 169 (1996) 193
He Youping, Zeng Jinbo, Wu Dexang, Su Genbo and Yan Mingshan, New technology of KDP crystal growth 169 (1996) 196
Helmrich, R. and H. Dabringhaus, Investigation of condensation and evaporation of alkali halide crystals by molecular beam methods. XIV. Development of two-dimensional islands on the (100) surface of LiF 169 (1996) 279
Heuken, M., see Taudt, W. 169 (1996) 243
Higashikawa, I., see Murooka, K.-i. 169 (1996) 485
Higuchi, M., see Tsai, T.-L. 169 (1996) 764
Hinks, D.G., see Zhang, K. 169 (1996) 73
Hirata, A., see Hu, W.-R. 169 (1996) 380
Hodby, J.W., see Chowdhury, A.J.S. 169 (1996) 405
Hong, S.-K., H.-G. Lee, J.-J. Lee, S.-G. Kim, K.-E. Pyun and H.-M. Park, Molecular beam epitaxy growth of indium-rich $In_xGa_{1-x}As/In_yAl_{1-y}As/InP$ structures towards high channel conductivity for a high electron mobility transistor using a linearly graded buffer layer 169 (1996) 435
Houng, M.P., see Sze, P.W. 169 (1996) 27
Hu, W.-R., A. Hirata and S.-i. Nishizawa, Diffusion dominated process for the crystal growth of a binary alloy 169 (1996) 380
Hu, W.R., see Han, J.H. 169 (1996) 129
Hu, X.B., see Liu, W.J. 169 (1996) 534
Huang Bingrong, see He Youping 169 (1996) 193
Huang, X.R., see Liu, W.J. 169 (1996) 534
Hung, C.Y., M.V. Weckwerth, A.F. Marshall, Y.C. Pao and J.S. Harris Jr., Observation of superstructure in high-quality pseudomorphic films of NiAl grown on GaAs 169 (1996) 201

Iida, S., see Hayakawa, Y. 169 (1996) 613
Imaeda, M., see Kawaguchi, T. 169 (1996) 94
Imafuji, O., see Hashimoto, T. 169 (1996) 185
Imai, T., see Takano, Y. 169 (1996) 621
Imaizumi, M., Y. Endoh, M. Suita, H. Sugimoto, K.-i. Ohtsuka, T. Isu and T. Ozeki, Gas-source molecular beam epitaxy of MgZnSSe for fabricating blue/green laser diodes 169 (1996) 293
Ishida, M., see Hashimoto, T. 169 (1996) 185
Ishida, M., see Wado, H. 169 (1996) 457
Ishida, M., see Suda, Y. 169 (1996) 672
Isu, T., see Imaizumi, M. 169 (1996) 293
Ito, S., see Kawaguchi, T. 169 (1996) 94
Itoh, K., see Hashimoto, T. 169 (1996) 185
Itoh, Y., see Sokolov, N.S. 169 (1996) 40
Izumi, K., Growth and lattice defects of hexamethylbenzene crystals 169 (1996) 325

Jang Rihong, see He Youping 169 (1996) 193
Jensen, K.F., see Salim, S. 169 (1996) 443
Jerman, G., see Palosz, W. 169 (1996) 20
Ji, Z., see Zhang, W. 169 (1996) 598
Jiang, J.H., see Liu, W.J. 169 (1996) 534
Jiang, S.S., see Liu, W.J. 169 (1996) 534
Jiang, Z., see Lu, X. 169 (1996) 665
Jie, W., see Ma, D. 169 (1996) 170
Jones, A.C., see Taudt, W. 169 (1996) 243
Jun, J., see Leszczynski, M. 169 (1996) 235

Kaigawa, K., see Kawaguchi, T. 169 (1996) 94
Kamel, M., see Tanaka, Y. 169 (1996) 299
Karandikar, S.C., see Sabharwal, S.C. 169 (1996) 304
Karpov, S.Yu., Yu.N. Makarov and M.S. Ramm, Analytical model of silicon carbide growth under free-molecular transport conditions 169 (1996) 491
Katayama, M., see Habuka, H. 169 (1996) 61
Kawaguchi, T., H. Kitayama, M. Imaeda, S. Ito, K. Kaigawa, T. Taniuchi and T. Fukuda, Stoichiometry of liquid-phase epitaxial grown $LiNb_{1-x}Ta_xO_3$ films on $LiNbO_3$ substrates 169 (1996) 94

Keshwani, K.S., see Sabharwal, S.C. 169 (1996) 304

Kidd, P., D.J. Dunstan, H.G. Colson, M.A. Lourenço, A. Sacedón, F. González-Sanz, L. González, Y. González, R. García, D. González, F.J. Pacheco and P.J. Goodhew, Comparison of the crystalline quality of step-graded and continuously graded InGaAs buffer layers 169 (1996) 649

Kikuzawa, M., see Hayakawa, Y. 169 (1996) 613

Kim, M., H.J. Thieme, G. Lippert and H.J. Osten, Optical in situ measurements of temperature and layer thickness in Si molecular beam epitaxy 169 (1996) 681

Kim, S.-B., J.-R. Ro, S.-J. Park and E.-H. Lee, Selective area epitaxy of GaAs and InGaAs by ultra-high vacuum chemical vapor deposition using triethylgallium, trimethylindium, arsine, and monoethylarsine 169 (1996) 429

Kim, S.-G., see Hong, S.-K. 169 (1996) 435

Kimura, M., see Udono, H. 169 (1996) 181

Kimura, M., S. Dost, H. Udono, A. Tanaka, T. Sukegawa and Z. Qin, A numerical analysis for the conversion phenomenon of GaAs to GaAsP on a GaP substrate in an LPE system 169 (1996) 697

Kina, H., Y. Yamada, Y. Maruta and Y. Tamura, ZnS:Mn thin-film electroluminescent devices prepared by metalorganic chemical vapor deposition 169 (1996) 33

Kitayama, H., see Kawaguchi, T. 169 (1996) 94

Klein, J.P., see El Moussaouiti, M. 169 (1996) 118

Klemenz, C., see Mukaida, M. 169 (1996) 715

Knight, C.A., see Nelson, J. 169 (1996) 795

Kohno, T., see Takeda, H. 169 (1996) 503

Kojima, H., see Tanaka, I. 169 (1996) 469

Koljonen, T., M. Sopanen, H. Lipsanen and T. Tuomi, Metalorganic vapor phase epitaxial growth of AlGaSb and AlGaAsSb using all-organometallic sources 169 (1996) 417

Komatsu, H., see Sazaki, G. 169 (1996) 355

Kotani, T., see Fujiwara, S. 169 (1996) 660

Kou, S., see Tao, Y. 169 (1996) 368

Koukitu, A., see Takahashi, N. 169 (1996) 463

Kovács, T., see Pfeifer, J. 169 (1996) 727

Koyama, T., see Hayakawa, Y. 169 (1996) 613

Kožíšek, Z. and P. Demo, Comment on 'Transient kinetics of binary nucleation by Z. Kožíšek and P. Demo' [J. Crystal Growth 132 (1993) 491] 169 (1996) 413

Krasiński, M.J. and R. Rolandi, Ex situ investigation of surface topography of as-grown potassium dihydrogen phosphate crystals by atomic force microscopy 169 (1996) 548

Krueger, C.W., S. Patnaik, C.A. Wang and M. Flytzani-Stephanopoulos, CH_3I vapor etching of GaAs in a vertical rotating-disk reactor 169 (1996) 51

Kukimoto, H., see Watanabe, K. 169 (1996) 223

Kumagawa, M., see Hayakawa, Y. 169 (1996) 613

Kurihara, K., see Sazaki, G. 169 (1996) 355

Kusunoki, T., see Nakajima, K. 169 (1996) 217

Kuwahara, K., see Takano, Y. 169 (1996) 621

Lairson, B.M., see Artymowicz, D.M. 169 (1996) 83

Lampe, S., see Taudt, W. 169 (1996) 243

Lan, C.W., Effect of axisymmetric magnetic fields on radial dopant segregation of floating-zone silicon growth in a mirror furnace 169 (1996) 269

Land, T.A., see Smolski, I. 169 (1996) 741

Larson, D., see Steiner, B. 169 (1996) 1

Laval, J.Y., see Androussi, Y. 169 (1996) 209

Lee, E.-H., see Kim, S.-B. 169 (1996) 429

Lee, H. and J.S. Harris Jr., Vapor phase epitaxy of GaN using $GaCl_3/N_2$ and NH_3/N_2 169 (1996) 689

Lee, H.-G., see Hong, S.-K. 169 (1996) 435

Lee, J.-J., see Hong, S.-K. 169 (1996) 435

Lee, J.D., see Smolski, I. 169 (1996) 741

Lee, S.-T., see Zhang, Y. 169 (1996) 722

Lefebvre, A., see Androussi, Y. 169 (1996) 209

Lei, X.-Y., P. Wan, N. Xu, C.-H. Zhou and N.-B. Ming, Coarsening phenomenon in two-dimensional colloidal aggregation and crystallization 169 (1996) 570

Leitch, A.W.R., see Botha, J.R. 169 (1996) 629

Le Marec, C., R. Guérin and P. Haldenwang, Radial macrosegregation induced by 3D patterns of solutal convection in upward Bridgman solidification 169 (1996) 147

Leszczynski, M., I. Grzegory, H. Teisseyre, T. Suski, M. Bockowski, J. Jun, J.M. Baranowski, S. Porowski and J. Domagala, The microstructure of gallium nitride monocrystals grown at high pressure 169 (1996) 235

Levine, L.E., see Steiner, B. 169 (1996) 1

Li, B., J.H. Chu, J.Q. Zhu, X.Q. Chen, J.Y. Cao and D.Y. Tang, Growth of $Hg_{1-x}Cd_xTe$ liquid phase epitaxial films on vicinal planes 169 (1996) 480

Li, H.D., see Cui, F.Z. 169 (1996) 557

Li Zhengdong, see He Youping 169 (1996) 193

Liang, J., see Lu, L. 169 (1996) 637

Lin, C.M., see Chou, W.C. 169 (1996) 747

Lippert, G., see Kim, M. 169 (1996) 681

Lipsanen, H., see Koljonen, T. 169 (1996) 417

Liu, K., see Lu, X. 169 (1996) 665

Liu, S., see Ma, D. 169 (1996) 170

Liu Song, and Ma Rongjun, Synthesis and structure of hydrated europium carbonate 169 (1996) 190

Liu, W.J., S.S. Jiang, X.R. Huang, X.B. Hu, W. Zeng, J.Q. Wei, J.Y. Wang, J.H. Jiang and Y. Han, Growth defects in Nb:KTP crystals observed by synchrotron radiation topography 169 (1996) 534

Lourenço, M.A., see Kidd, P. 169 (1996) 649

Lu, H.B., see Cui, F.Z. 169 (1996) 557

Lu, L., S. Feng, J. Liang, Z. Wang, J. Wang, Y. Wang and W. Ge, Characterization of deep

centers in AlGaAs/InGaAs/GaAs pseudomorphic HEMT structures grown by molecular beam epitaxy and hydrogen treatment 169 (1996) 637
Lu, L., S. Feng, J. Xu, H. Yang, Z. Wang, J. Wang, Y. Wang and W. Ge, Deep centers in AlGaAs/GaAs GRIN-SCH SQW laser structures grown by MBE and MOCVD 169 (1996) 643
Lu, X., Z. Jiang, K. Liu, H. Zhu, X. Zhang and X. Wang, Co-evaporative Sb doping and crystalline quality in Si molecular beam epitaxy 169 (1996) 665
Lubyshev, D.I., see González-Borrero, P.P. 169 (1996) 424
Lukasiewicz, T., see Frukacz, Z. 169 (1996) 98
Lunk, H.-J., see Pfeifer, J. 169 (1996) 727

Ma, C.L., see Cui, F.Z. 169 (1996) 557
Ma, D., W. Jie, S. Liu and W. Xu, Solute redistribution and growth velocity response in directional solidification process 169 (1996) 170
Ma Rongjun, see Liu Song 169 (1996) 190
Macicek, J.J., see Nihtianova, D.D. 169 (1996) 527
Magnanini, R., see Bignazzi, A. 169 (1996) 450
Makarov, Yu.N., see Karpov, S.Yu. 169 (1996) 491
Malik, M.A., see Taudt, W. 169 (1996) 243
Malm, J.-O., see Deppert, K. 169 (1996) 13
Marega Jr., E., see González-Borrero, P.P. 169 (1996) 424
Markgraf, S.A., see Tsai, T.-L. 169 (1996) 759
Markgraf, S.A., see Tsai, T.-L. 169 (1996) 764
Marshall, A.F., see Hung, C.Y. 169 (1996) 201
Maruta, Y., see Kina, H. 169 (1996) 33
Matkowskii, A., see Frukacz, Z. 169 (1996) 98
Matsumoto, K., see Fujiwara, S. 169 (1996) 660
Mayer, K. and D. Woermann, Influence of a polycrystalline precipitation zone on the growth of single crystals using a gel method: growth of single crystals of $PbHPO_4$ 169 (1996) 317
Mayusumi, M., see Habuka, H. 169 (1996) 61
McFadden, G.B., see Coriell, S.R. 169 (1996) 773
Ming, N.-B., see Lei, X.-Y. 169 (1996) 570
Mitchell, J., see Zhang, K. 169 (1996) 73
Miyashita, S., see Sazaki, G. 169 (1996) 355
Miyazawa, S., see Mukaida, M. 169 (1996) 715
Mogilevsky, R., see Zhang, K. 169 (1996) 73
Momirlan, M., see Badescu, V. 169 (1996) 309
Momose, M., see Watanabe, K. 169 (1996) 223
Motogaito, A., see Udono, H. 169 (1996) 181
Mücklich, F., see Scholz, U. 169 (1996) 575
Mücklich, F., see Scholz, U. 169 (1996) 578
Mukaida, M., S. Miyazawa, C. Klemenz and H.J. Scheel, Structural characterization of *a*-axis oriented $YBa_2Cu_3O_x$ films grown by liquid phase epitaxy 169 (1996) 715
Mukherjee, D.K., V. Prasad, P. Dutta and T. Yuan, Liquid crystal visualization of the effects of crucible and crystal rotation on Cz melt flows 169 (1996) 136
Müller, G., see Baumgartl, J. 169 (1996) 582
Munekata, H., see Watanabe, K. 169 (1996) 223
Murooka, K.-i., I. Higashikawa and Y. Gomei, Growth rate and deposition process of silicon carbide film by low-pressure chemical vapor deposition 169 (1996) 485
Murray, B.T., see Coriell, S.R. 169 (1996) 773

Nada, H. and Y. Furukawa, Anisotropic growth kinetics of ice crystals from water studied by molecular dynamics simulation 169 (1996) 587
Nagaki, Y., see Takano, Y. 169 (1996) 621
Nagoya, T., see Habuka, H. 169 (1996) 61
Nakada, T., see Sazaki, G. 169 (1996) 355
Nakajima, K. and T. Kusunoki, Constant temperature LEC growth of InGaAs ternary bulk crystals using the double crucible method 169 (1996) 217
Neamţu, C., see Darabont, Al. 169 (1996) 89
Nelson, J. and C.A. Knight, A new technique for growing crystals from the vapor 169 (1996) 795
Nenov, A.T., see Shumov, D.P. 169 (1996) 519
Nenov, A.T., see Nihtianova, D.D. 169 (1996) 527
Nicoara, D., see Nicoara, I. 169 (1996) 102
Nicoara, D., see Vizman, D. 169 (1996) 161
Nicoara, I., D. Vizman and D. Nicoara, Thermal stresses in shaped semi-transparent crystals 169 (1996) 102
Nicoara, I., see Vizman, D. 169 (1996) 161
Nihtianova, D.D., see Shumov, D.P. 169 (1996) 519
Nihtianova, D.D., D.P. Shumov, J.J. Macicek and A.T. Nenov, Inclusions in LiB_3O_5 crystals, obtained by the top-seeded solution growth method in the Li_2O–B_2O_3 system. Part 2 169 (1996) 527
Nikolic, Z.S., see Scholz, U. 169 (1996) 578
Nikolov, V., see Solé, R. 169 (1996) 600
Nishinaga, T., see Shen, X.Q. 169 (1996) 607
Nishizawa, S.-i., see Hu, W.-R. 169 (1996) 380

O'Brien, P., see Taudt, W. 169 (1996) 243
Ohtani, K., see Wado, H. 169 (1996) 457
Ohtsuka, K.-i., see Imaizumi, M. 169 (1996) 293
Okuyama, K., see Habuka, H. 169 (1996) 61
Osten, H.J., see Kim, M. 169 (1996) 681
Otálora, F. and J.M. García-Ruiz, Computer model of the diffusion/reaction interplay in the gel acupuncture method 169 (1996) 361
Ottenwälder, D., see Geiger, M. 169 (1996) 625
Overney, R.M., see Sokolov, N.S. 169 (1996) 40
Oya, S.-i., see Hashimoto, S. 169 (1996) 376
Ozeki, T., see Imaizumi, M. 169 (1996) 293

Pacheco, F.J., see Kidd, P. 169 (1996) 649
Palosz, W., K. Grasza, D. Gillies and G. Jerman, Growth of cadmium–zinc telluride crystals by controlled seeding "contactless" physical vapor transport 169 (1996) 20
Pao, Y.C., see Hung, C.Y. 169 (1996) 201
Park, H.-M., see Hong, S.-K. 169 (1996) 435

Park, S.-J., see Kim, S.-B. 169 (1996) 429
Patnaik, S., see Krueger, C.W. 169 (1996) 51
Perlov, D., see Roth, M. 169 (1996) 734
Petitprez, E., see González-Borrero, P.P. 169 (1996) 424
Petzow, G., see Scholz, U. 169 (1996) 575
Petzow, G., see Scholz, U. 169 (1996) 578
Pfeifer, J., E. Badaljan, P. Tekula-Buxbaum, T. Kovács, O. Geszti, A.L. Tóth and H.-J. Lunk, Growth and morphology of $W_{18}O_{49}$ crystals produced by microwave decomposition of ammonium paratungstate 169 (1996) 727
Pieters, I.Y., see De Maeyer, E.A.P. 169 (1996) 539
Pines, V., A. Chait and M. Zlatkowski, Anomaly in dendritic growth data – effect of density change upon solidification 169 (1996) 798
Plachke, D., see Scholz, U. 169 (1996) 575
Porowski, S., see Leszczynski, M. 169 (1996) 235
Pracka, I., see Frukacz, Z. 169 (1996) 98
Prasad, V., see Mukherjee, D.K. 169 (1996) 136
Prasad, V., see Zhang, H. 169 (1996) 250
Pyun, K.-E., see Hong, S.-K. 169 (1996) 435

Qin, Z., see Kimura, M. 169 (1996) 697

Radice, M., see Bignazzi, A. 169 (1996) 450
Rai, R.N., see Rai, U.S. 169 (1996) 563
Rai, U.S. and R.N. Rai, Studies on physico-chemical properties of the eutectic and monotectic in the urea–p. chloronitrobenzene system 169 (1996) 563
Raman, R., see Saghir, M.Z. 169 (1996) 110
Ramm, M.S., see Karpov, S.Yu. 169 (1996) 491
Recker, C., see Geiger, M. 169 (1996) 625
Ren, H.W., see Shen, X.Q. 169 (1996) 607
Ro, J.-R., see Kim, S.-B. 169 (1996) 429
Rodríguez-Clemente, R., see Gómez-Morales, J. 169 (1996) 331
Rodríguez-Clemente, R. and J. Gómez-Morales, Microwave precipitation of $CaCO_3$ from homogeneous solutions 169 (1996) 339
Rolandi, R., see Krasiński, M.J. 169 (1996) 548
Rosenbaum, D.F. and C.F. Zukoski, Protein interactions and crystallization 169 (1996) 752
Roth, M. and D. Perlov, Growth of barium borate crystals from sodium fluoride solutions 169 (1996) 734
Rudneva, E.B., see Smolski, I. 169 (1996) 741
Ruiz, X., see Solé, R. 169 (1996) 600
Rushworth, S., see Taudt, W. 169 (1996) 243

Sabharwal, S.C., Sangeeta, D.G. Desai, S.C. Karandikar, A.K. Chauhan, A.K. Sangiri, K.S. Keshwani and M.N. Ahuja, Effect of non-stoichiometry on some properties of lead tungstate single crystals 169 (1996) 304
Sacedón, A., see Kidd, P. 169 (1996) 649
Sadra, K., Techniques for molecular beam epitaxy of multiple-wavelength vertical-cavity laser arrays 169 (1996) 175
Saghir, M.Z., R. Abbaschian and R. Raman, Numerical analysis of thermocapillary convection in axisymmetric liquid encapsulated InBi 169 (1996) 110
Sakurai, T., see Hayakawa, Y. 169 (1996) 613
Salim, S., C.A. Wang, R.D. Driver and K.F. Jensen, In situ concentration monitoring in a vertical OMVPE reactor by fiber-optics-based Fourier transform infrared spectroscopy 169 (1996) 443
Sammelselg, V., see Aarik, J. 169 (1996) 496
Samuelson, L., see Deppert, K. 169 (1996) 13
Sangeeta, see Sabharwal, S.C. 169 (1996) 304
Sangiri, A.K., see Sabharwal, S.C. 169 (1996) 304
Sasaki, T., see Takano, Y. 169 (1996) 621
Sauerländer, F., see Taudt, W. 169 (1996) 243
Sazaki, G., K. Kurihara, T. Nakada, S. Miyashita and H. Komatsu, A novel approach to the solubility measurement of protein crystals by two-beam interferometry 169 (1996) 355
Scheel, H.J., see Mukaida, M. 169 (1996) 715
Scholz, F., see Geiger, M. 169 (1996) 625
Scholz, U., D. Plachke, W. Yuan, H.-J. Carstanjen, F. Mücklich and G. Petzow, On the influence of impurities in beryllium single crystal growth 169 (1996) 575
Scholz, U., Z.S. Nikolic, F. Mücklich and G. Petzow, Determination and modification of the thermal conditions in a double ellipsoid mirror furnace 169 (1996) 578
Schultz, A.J., see Zhang, K. 169 (1996) 73
Schumann, H., see Geiger, M. 169 (1996) 625
Sebastian, P.J., see Calixto, E. 169 (1996) 287
Seki, H., see Takahashi, N. 169 (1996) 463
Serrano, M.D., see Bermúdez, V. 169 (1996) 409
Seyssiecq, I., S. Veesler and R. Boistelle, A non-immersed induction conductivity system for controlling supersaturation in corrosive media: the case of gibbsite crystals agglomeration in Bayer liquors 169 (1996) 124
Shang, S.X., see Zeng, J.M. 169 (1996) 474
Shen, X.Q., H.W. Ren, M. Tanaka and T. Nishinaga, Real-time observations of faceting and shrinkage processes of disk-shaped mesas in GaAs molecular beam epitaxy on GaAs(111)B substrates 169 (1996) 607
Shibuya, Y., see Tanaka, I. 169 (1996) 469
Shimada, M., see Habuka, H. 169 (1996) 61
Shimamura, K., see Takeda, H. 169 (1996) 503
Shimamura, K., see Chani, V.I. 169 (1996) 604
Shin, H.Y., see Chou, W.C. 169 (1996) 747
Shirafuji, J., see Hashimoto, T. 169 (1996) 185
Shirakawa, T., see Fujiwara, S. 169 (1996) 660
Shumov, D.P., A.T. Nenov and D.D. Nihtianova, Inclusions in LiB_3O_5 crystals obtained by the top-seeded solution growth method in the Li_2O–B_2O_3 system. Part 1 169 (1996) 519
Shumov, D.P., see Nihtianova, D.D. 169 (1996) 527

Shusterman, Yu.V., see Sokolov, N.S. 169 (1996) 40
Siimon, H., see Aarik, J. 169 (1996) 496
Smolski, I., J.J. De Yoreo, N.P. Zaitseva, J.D. Lee, T.A. Land and E.B. Rudneva, Oriented liquid inclusions in KDP crystals 169 (1996) 741
Sokolov, N.S., J.C. Alvarez, S.V. Gastev, Yu.V. Shusterman, I. Takahashi, Y. Itoh, J. Harada and R.M. Overney, High quality CaF_2 layers on Si(111) with type-A epitaxial relation at the interface 169 (1996) 40
Solans, X., see Solé, R. 169 (1996) 600
Solé, R., V. Nikolov, X. Ruiz, Jna. Gavaldà, X. Solans, M. Aguiló and F. Díaz, Growth of β-$KGd_{1-x}Nd_x(WO_4)_2$ single crystals in $K_2W_2O_7$ solvents 169 (1996) 600
Söllner, J., see Taudt, W. 169 (1996) 243
Solskii, I., see Frukacz, Z. 169 (1996) 98
Sopanen, M., see Koljonen, T. 169 (1996) 417
Steiner, B., L.E. Levine, M. Brown and D. Larson, Residual disorder in low pressure, low thermal gradient liquid encapsulated Czochralski gallium arsenide observed in high resolution synchrotron diffraction imaging 169 (1996) 1
Su Genbo, see He Youping 169 (1996) 193
Su Genbo, see He Youping 169 (1996) 196
Suda, Y., M. Ishida and M. Yamashita, Ar^+-laser-assisted subatomic-layer epitaxy of Si 169 (1996) 672
Sugak, D., see Frukacz, Z. 169 (1996) 98
Sugimoto, H., see Imaizumi, M. 169 (1996) 293
Sugino, T., see Hashimoto, T. 169 (1996) 185
Suita, M., see Imaizumi, M. 169 (1996) 293
Sukegawa, T., see Udono, H. 169 (1996) 181
Sukegawa, T., see Kimura, M. 169 (1996) 697
Sun, C.Y., see Chou, W.C. 169 (1996) 747
Sun, J., see Zhang, Y. 169 (1996) 722
Sun, Z.W., see Han, J.H. 169 (1996) 129
Suski, T., see Leszczynski, M. 169 (1996) 235
Sze, P.W., N.F. Wang, M.P. Houng, Y.H. Wang, Y.T. Cherng and C.H. Wang, Characteristics of ZnCdTe grown on (100) GaAs substrate by MOCVD 169 (1996) 27

Tabarrok, B., see Ye, X. 169 (1996) 704
Takahashi, I., see Sokolov, N.S. 169 (1996) 40
Takahashi, N., A. Koukitu and H. Seki, Effect of Ag addition on $YBa_2Cu_3O_{7-\delta}$ superconducting thin films prepared by mist microwave-plasma chemical vapor deposition 169 (1996) 463
Takano, Y., T. Sasaki, Y. Nagaki, K. Kuwahara, S. Fuke and T. Imai, Two-step growth of InP on GaAs substrates by metalorganic vapor phase epitaxy 169 (1996) 621
Takeda, H., K. Shimamura, T. Kohno and T. Fukuda, Growth and characterization of $La_3Nb_{0.5}Ga_{5.5}O_{14}$ single crystals 169 (1996) 503
Tamura, Y., see Kina, H. 169 (1996) 33
Tanaka, A., see Udono, H. 169 (1996) 181
Tanaka, A., see Kimura, M. 169 (1996) 697
Tanaka, I., Y. Shibuya and H. Kojima, Crystal growth of pure and Zn-doped $CuGeO_3$ by the floating zone (FZ) method 169 (1996) 469
Tanaka, M., see Shen, X.Q. 169 (1996) 607
Tanaka, Y., M. Kamel and Y. Gotoh, Growth of Ce thin film on a Mo(110) surface 169 (1996) 299
Tang, D.Y., see Li, B. 169 (1996) 480
Taniuchi, T., see Kawaguchi, T. 169 (1996) 94
Tao, Y. and S. Kou, Segregation control in vertical Bridgman crystal growth 169 (1996) 368
Taudt, W., S. Lampe, F. Sauerländer, J. Söllner, H. Hamadeh, M. Heuken, A.C. Jones, S. Rushworth, P. O'Brien and M.A. Malik, Nitrogen doping of ZnSe with trimethylsilylazide, triallylamine or bisditrimethylsilylamidozinc during metalorganic vapour phase epitaxy 169 (1996) 243
Teisseyre, H., see Leszczynski, M. 169 (1996) 235
Tekula-Buxbaum, P., see Pfeifer, J. 169 (1996) 727
Terakoshi, Y., see Hashimoto, T. 169 (1996) 185
Thieme, H.J., see Kim, M. 169 (1996) 681
Torrent-Burgués, J., see Gómez-Morales, J. 169 (1996) 331
Tóth, A.L., see Pfeifer, J. 169 (1996) 727
Tsai, C.T., see Chou, W.C. 169 (1996) 747
Tsai, T.-L., S.A. Markgraf and R. Dieckmann, Floating-zone growth and characterization of Fe_2SiO_4 single crystals 169 (1996) 759
Tsai, T.-L., S.A. Markgraf, M. Higuchi and R. Dieckmann, Growth of $(Fe_xMg_{1-x})_2SiO_4$ single crystals by the double pass floating zone method 169 (1996) 764
Tuomi, T., see Koljonen, T. 169 (1996) 417

Udono, H., A. Motogaito, M. Kimura, A. Tanaka and T. Sukegawa, Suppression of twins in GaAs layers grown on a GaP(111)B substrate by liquid phase epitaxy 169 (1996) 181
Udono, H., see Kimura, M. 169 (1996) 697
Uustare, T., see Aarik, J. 169 (1996) 496

Vandewalle, N., M. Ausloos and R. Cloots, Fractal grain boundaries in growth competition 169 (1996) 79
Vasylechko, L., see Frukacz, Z. 169 (1996) 98
Veesler, S., see Seyssiecq, I. 169 (1996) 124
Verbeeck, R.M.H., see De Maeyer, E.A.P. 169 (1996) 539
Vizman, D., see Nicoara, I. 169 (1996) 102
Vizman, D., I. Nicoara and D. Nicoara, On the factors affecting the isotherm shape during Bridgman growth of semi-transparent crystals 169 (1996) 161
Volkozub, A.V., see Chowdhury, A.J.S. 169 (1996) 405

Wado, H., K. Ohtani and M. Ishida, Epitaxial growth of SiGe on Al_2O_3 using Si_2H_6 gas and Ge solid source molecular beam epitaxy 169 (1996) 457
Walsh, D., see Ye, X. 169 (1996) 704

Wan, P., see Lei, X.-Y. 169 (1996) 570
Wang, C.A., see Krueger, C.W. 169 (1996) 51
Wang, C.A., see Salim, S. 169 (1996) 443
Wang, C.H., see Sze, P.W. 169 (1996) 27
Wang, H., see Zeng, J.M. 169 (1996) 474
Wang, J., see Lu, L. 169 (1996) 637
Wang, J., see Lu, L. 169 (1996) 643
Wang, J.Y., see Liu, W.J. 169 (1996) 534
Wang, M., see Zeng, J.M. 169 (1996) 474
Wang, N.F., see Sze, P.W. 169 (1996) 27
Wang, X., see Lu, X. 169 (1996) 665
Wang, Y., see Zhang, K. 169 (1996) 73
Wang, Y., see Lu, L. 169 (1996) 637
Wang, Y., see Lu, L. 169 (1996) 643
Wang, Y.H., see Sze, P.W. 169 (1996) 27
Wang, Z., see Zeng, J.M. 169 (1996) 474
Wang, Z., see Lu, L. 169 (1996) 637
Wang, Z., see Lu, L. 169 (1996) 643
Wanklyn, B.M.R., see Chowdhury, A.J.S. 169 (1996) 405
Watanabe, K., M. Momose, K. Hara, H. Munekata and H. Kukimoto, Selective area chemical beam epitaxy of GaAs using Ga_2O_3 as a mask layer 169 (1996) 223
Watanabe, K., Growth of minute barium ferrite single crystals from a Na_2O–B_2O_3 flux system 169 (1996) 509
Weckwerth, M.V., see Hung, C.Y. 169 (1996) 201
Wei, J.Q., see Liu, W.J. 169 (1996) 534
Winterfeld, J., see Geiger, M. 169 (1996) 625
Woermann, D., see Mayer, K. 169 (1996) 317
Wondre, F.R., see Chowdhury, A.J.S. 169 (1996) 405
Wu Dexang, see He Youping 169 (1996) 196
Wu, X.-B., X. Geng and Z.-Y. Guo, Fundamental study of crystal/melt interface shape change in Czochralski crystal growth 169 (1996) 786

Xie, J.C., see Han, J.H. 169 (1996) 129
Xie, L., see Zhang, Y. 169 (1996) 722
Xu, J., see Lu, L. 169 (1996) 643
Xu, N., see Lei, X.-Y. 169 (1996) 570
Xu, W., see Ma, D. 169 (1996) 170

Yamada, Y., see Kina, H. 169 (1996) 33
Yamaguchi, A., see Hashimoto, S. 169 (1996) 376
Yamashita, M., see Suda, Y. 169 (1996) 672
Yan Mingshan, see He Youping 169 (1996) 196
Yan, S., see Zhang, W. 169 (1996) 598
Yanagida, H., see Hayakawa, Y. 169 (1996) 613
Yang, H., see Lu, L. 169 (1996) 643
Ye, X., B. Tabarrok and D. Walsh, The influence of thermosolutal convection on CdTe growth by the traveling heater method 169 (1996) 704
Yi, W.S., see Choe, K.S. 169 (1996) 227
Yoshikawa, A., see Hashimoto, T. 169 (1996) 185
Yu Xianchun, see He Youping 169 (1996) 193
Yuan, T., see Mukherjee, D.K. 169 (1996) 136
Yuan, W., see Scholz, U. 169 (1996) 575

Zaitseva, N.P., see Smolski, I. 169 (1996) 741
Zeng Jinbo, see He Youping 169 (1996) 196
Zeng, J.M., H. Wang, S.X. Shang, Z. Wang and M. Wang, Preparation and characterization of epitaxial MgO thin film by atmospheric-pressure metalorganic chemical vapor deposition 169 (1996) 474
Zeng, W., see Liu, W.J. 169 (1996) 534
Zhang, H., V. Prasad and D.F. Bliss, Modeling of high pressure, liquid-encapsulated Czochralski growth of InP crystals 169 (1996) 250
Zhang, K., R. Mogilevsky, D.G. Hinks, J. Mitchell, A.J. Schultz, Y. Wang and V. Dravid, Crystal growth of $(La,Sr)_2CuO_4$ by float zone melting 169 (1996) 73
Zhang, W., S. Yan and Z. Ji, Effective segregation coefficient and steady state segregation coefficient of germanium in Czochralski silicon 169 (1996) 598
Zhang, X., see Lu, X. 169 (1996) 665
Zhang, Y., L. Xie, Z. Zhou, J. Sun and S.-T. Lee, Characteristics of diamond crystals deposited on quartz substrates by chemical vapor deposition 169 (1996) 722
Zhao Qingran, see He Youping 169 (1996) 193
Zhou, C.-H., see Lei, X.-Y. 169 (1996) 570
Zhou, L.F., see Cui, F.Z. 169 (1996) 557
Zhou, Z., see Zhang, Y. 169 (1996) 722
Zhu, H., see Lu, X. 169 (1996) 665
Zhu, J.Q., see Li, B. 169 (1996) 480
Žižić, B., see Čabrić, B. 169 (1996) 199
Zlatkowski, M., see Pines, V. 169 (1996) 798
Zukoski, C.F., see Rosenbaum, D.F. 169 (1996) 752

ELSEVIER

Journal of Crystal Growth 169 (1996) 811–813

JOURNAL OF CRYSTAL GROWTH

Subject index

Apparatus
– for agglomeration
– – of gibbsite 124
– for beryllium growth
– – by mirror furnace 578
– for indium gallium arsenide growth
– – by double crucible 217
– for pure crystals
– – of potassium magnesium ferrite 89
– for vapor growth
– – of ice 795

Beryllium 575, 578

Computer simulation
– of conversion phenomenon 697
– of epitaxial growth 61
– of heat flow 269
– of moving boundaries 161
– of protein crystallization 361
– of stress field 102
– of YBCO 79
Crystal growth, special
– of nanostructures 13
Convection 110, 147, 582, 773

Dendritic growth
– theory of density change upon solidification 798
Device characterization
– electroluminescent 33
– electronic devices 201, 227, 637, 649
– heterojuntion 201, 227, 629
– induced conductivity 124
– lasers 293, 643
– quantum wells or dots 424, 629
– transistors 435, 637
Diamond 722
Diffusional control 380
– of faceting 607
– of protein crystal growth 361
– of solute redistribution 170
Doping of, in
– antimony in silicon 665
– germanium in silicon 598
– nitrogen in zinc selenide 243
– silver in YBCO 463
– tellurium in gallium antimonide 450
– zinc in copper germanate 469

Electronic devices, see Device characterization
Etching
– chemical 51, 409
Eutectic growth
– of urea–p. chloronitrobenzene 563

Gallium
– arsenide 1, 13

Heterojunction, see Device characterization
Hydrodynamics, see Convection

Kinetics
– of formation 83
– of growth 79, 279, 309, 347, 393, 429, 491, 496, 548, 570, 587, 607, 629, 697, 773
– of interface control 170, 201, 557, 629
– of nucleation 181, 331, 413
– of purification 339

Lasers, see Device characterization
Lysozyme 355, 752

Material analysis
– by atomic force microscopy
– – of potassium dihydrogen phosphate 548
– by optical absorption
– – of lithium niobate 98
– – of yttrium ortho-aluminate 98
– by X-ray
– – of silicon germanium 681
Melt growth technique
– by Bridgman–Stockbarger method
– – of lead–thallium 147
– – of potassium magnesium fluoride 89
– – of semitransparent fluorides 161
– – of sodium nitrate 368
– – theory of *g*-jitter 582
– by Czochralski method
– – of gallium arsenide 1
– – of indium phosphide 250

– – of lanthanum niobium gallate 503
– – of lead tungstate 304
– – of liquid crystals 136
– – of lithium niobate 409
– – of silicon 598
– – theory of melt/crystal interface 786
– by edge-defined film-fed growth
– – of sapphire 102
– by floating zone method
– – of copper germanate 469
– – of iron magnesium sulphate (olivine) 764
– – of iron sulphate 759
– – of lanthanum strontium cuprate 73
– – of silicon 269
– by travelling heater method
– – of cadmium telluride 704
– – theory of
– – – diffusional dominated process 380
– – – heat transport 704
– by zone melting
– – of indium bismuth 110
– – of indium gallium arsenide 217
– – of mercury 129
Microgravity, growth under
– of indium bismuth 110
– of iron magnesium sulphate (olivine) 764
– theory of fluctuation of *g*-jitter 582
Morphological stability
– of potassium dihydrogen phosphate 741

Nucleation
– of binary vapor 413
– of calcium carbonate 331
– of dislocations 209
Numbers
– Rayleigh 147

Phase diagram
– of barium ferrite 509
– of calcium phosphate 557
– of hydroxy apatite 557
– of indium gallium arsenide 217
– of proteins 355
– of urea–p. chloronitrobenzene 563
Precursor
– for calcium carbonate 339
– for phosphides 625
Proteins 355

Quantum dots, see Device characterization
Quantum wells, see Device characterization

Silicon 61, 598, 665, 672
– carbide 485, 491
Solid growth technique
– by hydrolysis
– – of carbonated apatite 539
– by recrystallization
– – of carbonated apatite 539
Solution growth technique
– by electrochemical deposition
– – of copper indium diselenide 287
– by flux method
– – of barium borate 734
– – of barium ferrite 509
– – of beta-potassium gadolinium tungstate 600
– – of BSCCO 405
– – of gel acupuncture 361
– – of potassium magnesium niobate arsenate 604
– – of potassium titanyl phosphate 534
– – of potassium zinc niobate arsenate 604
– by gel method
– – of lead hydrogen phosphate 317
– by Holden technique
– – of potassium dihydrate 196
– by hydrothermal growth
– – of lithium triborate 519, 527
– by low temperature method
– – of ammonium dihydrogen phosphate 325
– – of cadmium zinc manganese telluride 747
– – of calcium sulphate hemihydrate 118
– – of hexahydrate nickel sulphate 193
– – of hexamethylbenzene 325
– – theory of step bouncing 773
– by microwave activation
– – of calcium carbonate 339
Statistical mechanics, molecular theory
– of ice 393, 587
– of YBCO 79
Stefan problem or moving boundary problem
– of fluorides 161
– of silicon 269
Superconductivity materials, high T_c
– bulk
– – of BSCCO 405
– – of YBCO 79
– film
– – of YBCO 463, 715
Superlattices, multilayers
– of platinum/cobalt 83
– of III–V compounds
Surface structure
– of ice–vapor interface 393
– of rutile 309
Synthesis
– of hydrated europium cuprate 190

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of silicon 672
– – of titanium oxide 496
– by liquid phase epitaxy
– – of gallium arsenide 181
– – of indium gallium arsenide 613
– – of lithium niobate 94
– – of mercury cadmium telluride 480

– – of YBCO 715
– by molecular beam epitaxy
– – of aluminum gallium arsenide 637
– – of calcium chloride 40
– – of cerium 299
– – of gallium antimonide 450
– – of gallium arsenide 223, 607, 649
– – of indium aluminum arsenide 435
– – of indium gallium arsenide 209, 424, 435, 637, 649
– – of indium phosphide 435
– – of nickel aluminium 201
– – of silicon 665, 681
– – theory of
– – – lateral thickness 175
– – – silicon carbide growth 491
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of aluminum gallium antimonide 417
– – – of aluminum gallium arsenide 227
– – – of aluminum gallium arsenide antimonide 417
– – – of diamond 722
– – – of gallium antimonide 417
– – – of gallium arsenide 227, 429, 629
– – – of gallium nitride 185
– – – of in situ monitoring 443
– – – of indium gallium arsenide 429
– – – of indium phosphide 621, 625
– – – of magnesium oxide 474
– – – of magnesium zinc selenide sulphide 293
– – – of silicon 61
– – – of silicon germanium 261
– – – of zinc cadmium telluride 27
– – – of zinc sulphide 33
– – – of zirconium selenide 243
Transistors, see Device characterization

Vapor growth technique
– by aerosol formation and reaction
– – of gallium arsenide 13
– by chemical transport
– – of copper indium diselenide 287
– – of gallium nitride 689
– – of silicon 61
– – of silicon carbide 485
– by evaporation and condensation
– – of β-Ca_2SiO_4 376
– – of cadmium zinc telluride 20
– – of ice 795
– – of lithium fluoride 279
– – of silicon germanium 261
– – of zinc selenide 660
– theory of 393

Whisker growth
– of tungsten oxide 727